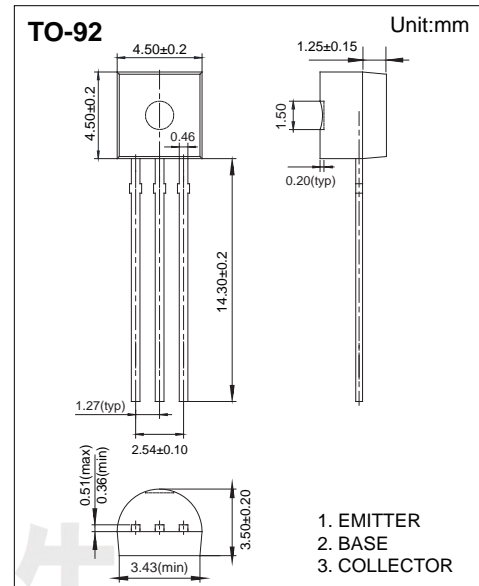


Transistor

PNP Transistor S9015

■ Features

- High Total Power Dissipation. ($P_C=0.45W$)
- High h_{FE} and Good Linearity
- Complementary to S9014



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-50	V
Collector - Emitter Voltage	V_{CE0}	-45	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-0.1	A
Collector Power Dissipation	P_C	0.45	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V_{CB0}	$I_C = -100 \mu A, I_E = 0$	-50			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 mA, I_B = 0$	-45			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu A, I_C = 0$	-5			
Collector cut-off current	I_{CBO}	$V_{CB} = -50 V, I_E = 0$			-0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.05	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 mA, I_B = -10mA$			-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100 mA, I_B = -10mA$			-1	
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -1mA$	60		1000	
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA, f = 30MHz$	150			MHz

■ Classification of h_{FE}

Rank	A	B	C	D
Range	60-150	100-300	200-600	400-1000

Transistor

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Typical Characteristics

